What is claimed is:

- 1. A processing apparatus, comprising:
 - a transfer chamber;

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- a plurality of processing chambers for processing therein a substrate to be processed, the processing chambers being coupled to the transfer chamber;
 - a number of electrostatic chucks which are provided in the processing chambers, to electrostatically adsorb the substrate to be processed thereto;
 - a transfer mechanism installed in the transfer chamber to transfer the substrate to be processed between the processing chambers and the transfer chamber; and
- a monatomic nitrogen atom supply unit for supplying dissociated monatomic nitrogen atoms into the processing chambers.
 - 2. A processing apparatus, comprising:
 - a transfer chamber;
- a first processing chamber coupled to the transfer chamber, the first processing chamber performing therein a first process on a substrate to be processed;
 - a second processing chamber coupled to the transfer chamber, the second processing chamber performing therein a second process on the substrate to be processed;
 - a transfer mechanism installed in the transfer chamber for

sequentially transferring the substrate to be processed into the first and second processing chamber;

electrostatic chucks provided in the first and the second processing chambers, the electrostatic chucks electrostatically adsorbing thereto the substrate to be processed; and

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- a monatomic nitrogen atom supply unit for supplying dissociated monatomic nitrogen atoms into the first and second processing chamber.
- 10 3. The processing apparatus of claim 1, wherein the monatomic nitrogen atom supply unit supplies the dissociated monatomic nitrogen atoms to a close proximity of the electrostatic chucks.
- 4. The processing apparatus of claim 2, wherein the monatomic nitrogen atom supply unit supplies the dissociated monatomic nitrogen atoms to a close proximity of the electrostatic chucks.
 - 5. The processing apparatus of claim 2, wherein the monatomic nitrogen atom supply unit supplies the dissociated monatomic nitrogen atoms into the transfer chamber.
 - 6. The processing apparatus of claim 2, further comprising a controller for controlling a supply timing of the dissociated monatomic nitrogen atoms from the monatomic nitrogen atom supply unit.

7. The processing apparatus of claim 2, wherein the monatomic nitrogen atom supply unit includes a pipe communicating with the processing chambers, an N_2 gas supply source for supplying an N_2 gas through the pipe, and an energy supply unit for applying energy to the N_2 gas in the pipe or in the processing chambers to convert the N_2 gas into the dissociated monatomic nitrogen atoms.

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- 8. The processing apparatus of claim 6, wherein the energy supply unit has an ultraviolet irradiation unit for irradiating ultraviolet ray to the N_2 gas.
 - 9. The processing apparatus of claim 6, wherein the pipe has a dielectric portion, and the energy supply unit has an induction coil wound around the dielectric portion and a high frequency power supply for applying a high frequency to the induction coil.
 - 10. The processing apparatus of claims 6, wherein the energy supply unit applies energy which is higher than the dissociation energy of the N_2 gas and lower than the ionization energy of the N_2 gas, to the N_2 gas.
 - 11. A processing method employing a processing apparatus, which includes a transfer chamber, a plurality of processing chambers coupled to the transfer chamber, to process therein a target substrate, and a number of electrostatic chucks provided in the

processing chambers to electrostatically adsorb the target substrate thereto, comprising the steps of:

transferring the target substrate from the transfer chamber into one of the processing chambers by using a transfer mechanism;

placing the target substrate on an electrostatic chuck displaced in said one processing chamber;

applying a direct current to an electrode embedded in the electrostatic chuck to electrostatically absorb the target substrate to the electrostatic chuck;

processing the target substrate in said one processing chamber, to thereby obtain a processed substrate;

terminating the application of the direct current to the electrostatic chuck;

supplying dissociated monatomic nitrogen atoms into said one processing chamber to remove charge on the electrostatic chuck; and

transferring the processed substrate into the transfer chamber using the transfer mechanism.

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- 12. The processing method of claim 11, wherein the dissociated monatomic nitrogen atoms are supplied near the electrostatic chucks.
- 25 13. A processing method using a processing apparatus, which includes a transfer chamber, a first processing chamber coupled

to the transfer chamber, for performing a first process on a target substrate therein, a second processing chamber coupled to the transfer chamber for performing a second process on the target substrate therein, and a first and second electrostatic chucks provided in the first and second processing chambers, respectively, to electrostatically adsorb the substrate thereto, comprising the steps of:

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transferring the target substrate from the transfer chamber into the first processing chamber using a transfer mechanism;

placing the target substrate on the first electrostatic chuck in the first processing chamber;

applying a direct current to an electrode of the first electrostatic chuck to electrostatically adsorb the target substrate to the first electrostatic chuck;

performing a first process on the target substrate in the first processing chamber to thereby obtain a processed substrate:

terminating the application of the direct current to the first electrostatic chuck;

supplying dissociated monatomic nitrogen atoms into the first processing chamber to remove charge on the first electrostatic chuck;

transferring the processed substrate into the transfer chamber using the transfer mechanism;

transferring the processed substrate from the transfer chamber into the second processing chamber;

placing the processed substrate on the second electrostatic chuck in the second processing chamber;

applying the direct current to an electrode of the second electrostatic chuck to electrostatically adsorb the processed substrate to the second electrostatic chuck; and

performing a second process on the processed substrate in the processed second processing chamber.

- 14. The processing method of claim 13, wherein the dissociated 10 monatomic nitrogen atoms are supplied near the electrostatic chucks.
 - 15. The processing method of claim 13, further comprising the step of supplying the dissociated monatomic nitrogen atoms into the transfer chamber.
 - 16. The processing method of claim 13, wherein the dissociated monatomic nitrogen atoms are produced by irradiating ultraviolet ray onto N_2 gas.

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17. The processing method of claim 13, wherein the dissociated monatomic nitrogen atoms are produced by applying energy, generated during application of a high frequency power to an induction coil, onto N_2 gas.

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18. The processing method of claim 13, wherein the dissociated

monatomic nitrogen atoms are produced by applying energy, higher than dissociation energy of N_2 and lower than ionization energy of N_2 , to the N_2 gas. 12. The processing method of claim 10, wherein the dissociated monatomic nitrogen atoms are supplied near the electrostatic chucks.

19. A processing apparatus, comprising:

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a processing chamber for processing therein a substrate to be processed;

an electrostatic chuck installed in the processing chamber, for adsorbing the substrate to be process thereto; and

a monatomic N atom supply unit for supplying dissociated monoatomic N atoms into the processing chamber.

20. A processing method employing a processing apparatus, which includes a processing chamber for processing a substrate to be processed and an electrostatic chuck for adsorbing the substrate to be process thereto, comprising the steps of:

mounting the substrate to be processed on the electrostatic chuck disposed in the processing chamber; and

supplying dissociated monatomic N atoms into the processing chamber.